



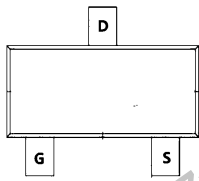
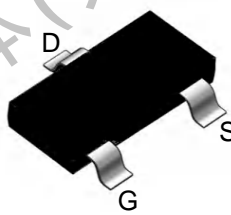
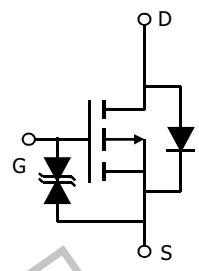
TM01EP02I5

P-Channel Enhancement Mosfet

<p>General Description</p> <ul style="list-style-type: none"> • Low R_{DS(ON)} • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>V_{DS} = -20V I_D = -1A R_{DS(ON)} = 280 mΩ (typ.) @ V_{GS} = -4.5V</p> <p>ESD protection</p> <p>100% UIS Tested 100% R_g Tested</p>
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I5:SOT-523

Marking: 39K OR 3139A

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V	-1	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V	-0.5	A
I _{DM}	Pulsed Drain Current	-4	A
P _D @T _A =25°C	Total Power Dissipation	0.3	W
T _{STG}	Storage Temperature Range	-55 to 175	°C
T _J	Operating Junction Temperature Range	-55 to 175	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient	---	178	°C/W
R	Thermal Resistance Junction Case	---	---	°C/W

TM01EP02I5

P-Channel Enhancement Mosfet

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Static Parameter	Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage		BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current		I_{DSS}	$V_{DS}=-20V, V_{GS}=0V, T_C=25^\circ\text{C}$			-1	μA
Gate-Body Leakage Current		I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage		$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.65	-1.0	V
Static Drain-Source On-Resistance		$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-1A$		280	320	m Ω
			$V_{GS}=-2.5V, I_D=-0.5A$		360	460	
			$V_{GS}=-1.8V, I_D=-0.3A$		---	---	
Diode Forward Voltage		V_{SD}	$I_S=-2A, V_{GS}=0V$		-0.8	-1.2	V
Maximum Body-Diode Continuous Current		I_S				-1	A
Dynamic Parameters							
Input Capacitance		C_{iss}	$V_{DS}=-10V, V_{GS}=0V, f=1\text{MHz}$		127		pF
Output Capacitance		C_{oss}			23		
Reverse Transfer Capacitance		C_{rss}			15		
Switching Parameters							
Total Gate Charge		Q_g	$V_{GS}=-4.5V, V_{DS}=-10V, I_D=-2A$		4.5		nC
Gate Source Charge		Q_{gs}			0.85		
Gate Drain Charge		Q_{gd}			1.4		
Reverse Recovery Charge		Q_{rr}	$I_F=-2A, di/dt=100A/\mu s$		2.3		ns
Reverse Recovery Time		t_{rr}			27		
Turn-on Delay Time		$t_{D(on)}$	$V_{GS}=-4.5V, V_{DD}=-10V, I_D=-1A, R_{GEN}=2.5\Omega$		6		ns
Turn-on Rise Time		t_r			30		
Turn-off Delay Time		$t_{D(off)}$			45		
Turn-off Fall Time		t_f			46		

TM01EP02I5

P-Channel Enhancement Mosfet

Typical Performance Characteristics

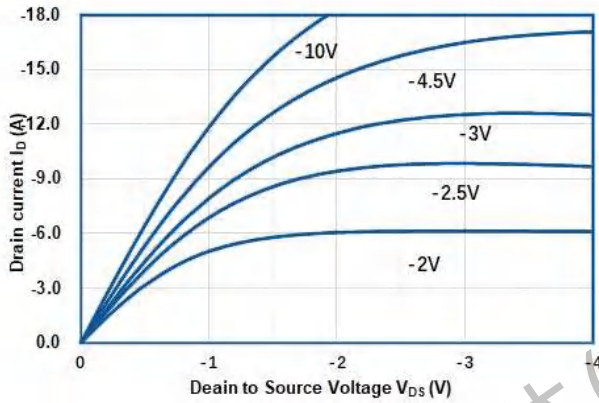


Figure1. Output Characteristics

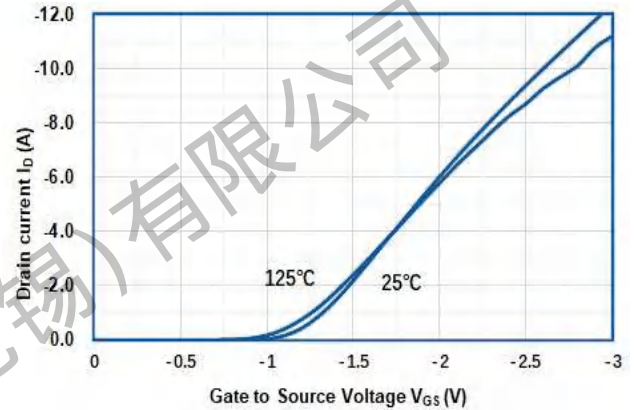


Figure2. Transfer Characteristics

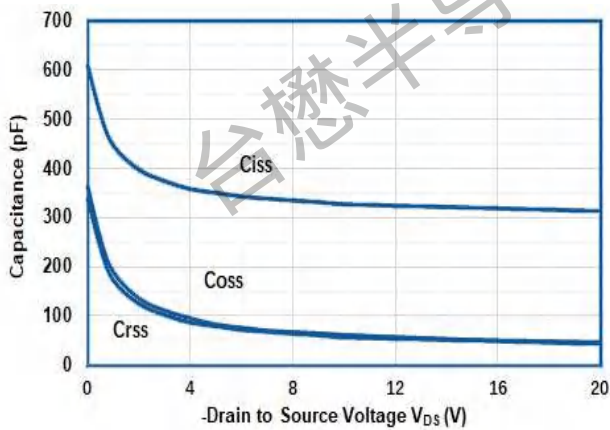


Figure3. Capacitance Characteristics

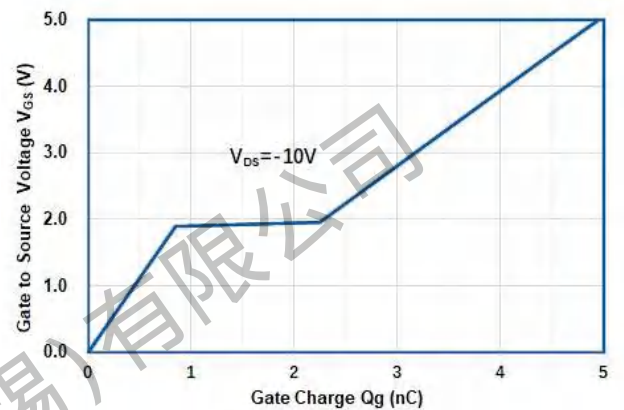


Figure4. Gate Charge

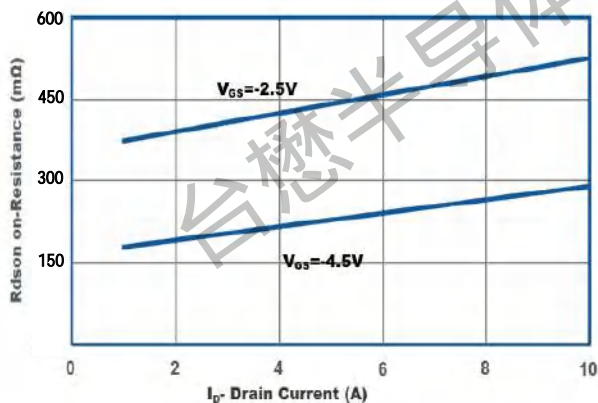


Figure5. Drain-Source on Resistance

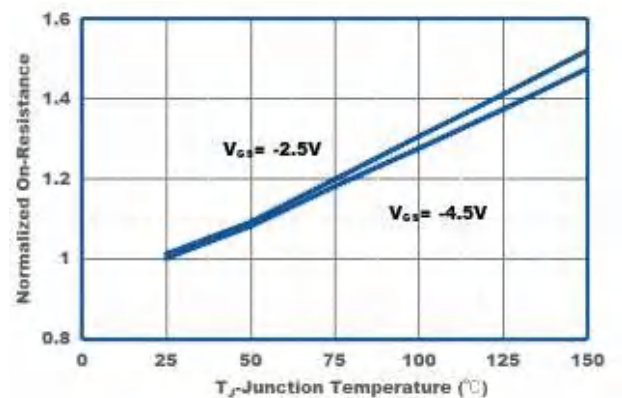


Figure6. Drain-Source on Resistance



TM01EP02I5

P-Channel Enhancement Mosfet

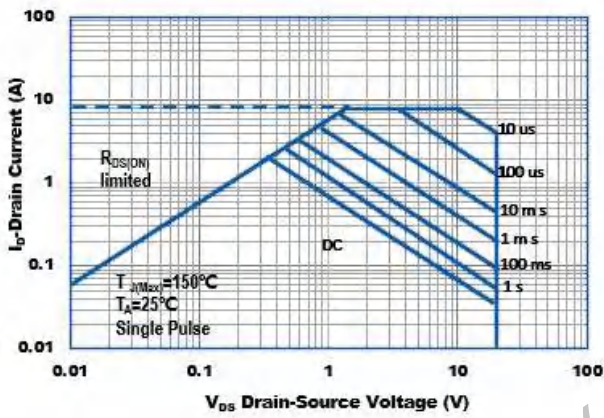


Figure7. Safe Operation Area

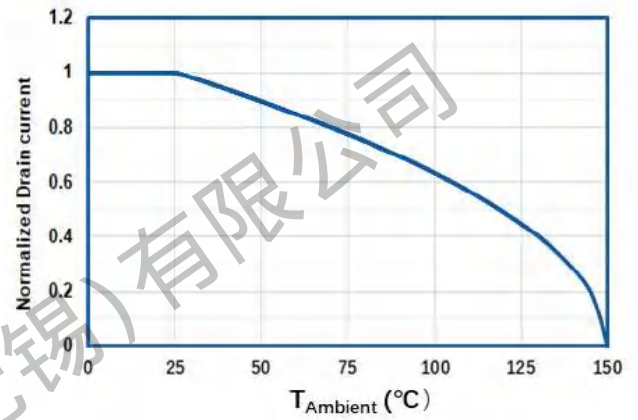


Figure8. Drain Current vs Ambient temperature

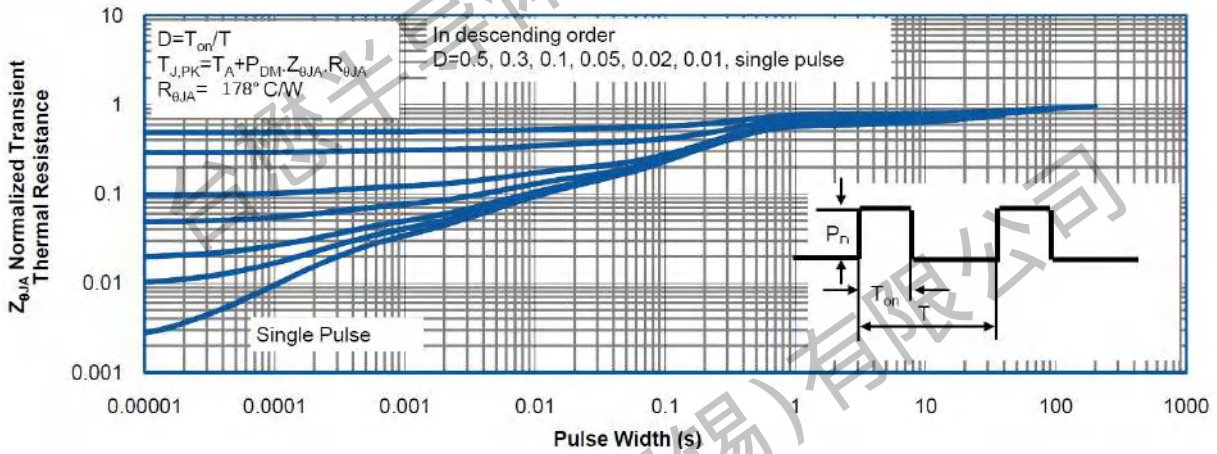


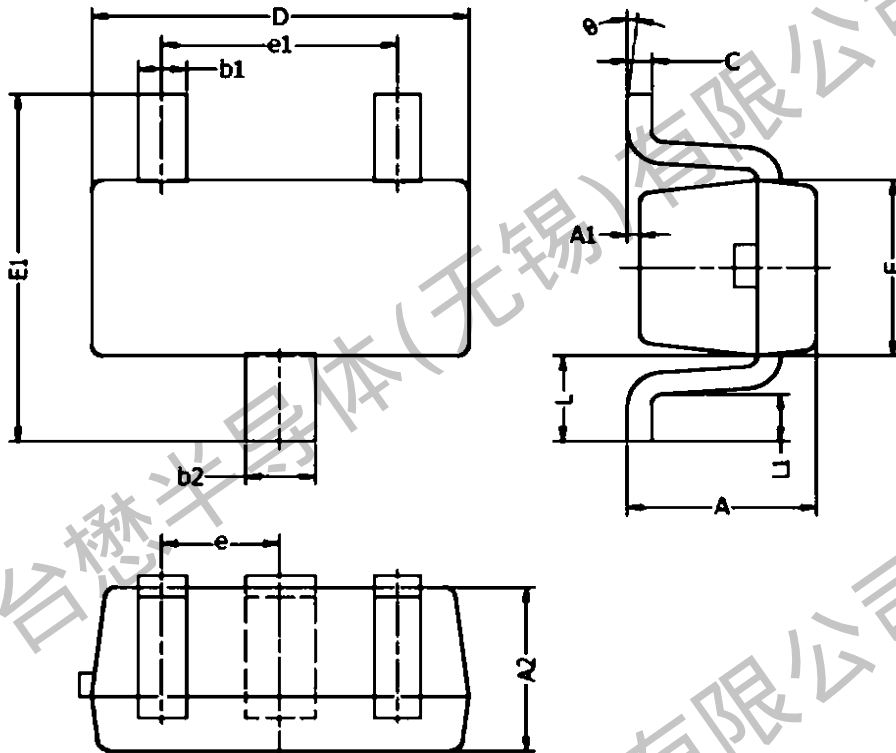
Figure9. Normalized Maximum Transient Thermal Impedance



TM01EP02I5

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Package Mechanical Data:SOT-523



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0°	8°	0°	8°

NOTES:

1. Above package outline conforms to JEITA EAJ ED-7500A SC-75A.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.



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Revision history:

Date	Rev	Description	Page
2023.06.21	23.06	Original	